

**1200V/40A Silicon Carbide Power Schottky Barrier Diode**

**Features**

- Rated to 1200V at 40 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- High temperature operation
- High frequency operation

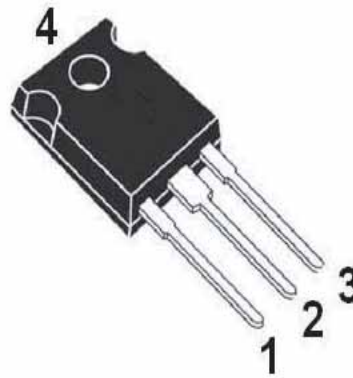
Key Characteristics		
$V_{RRM}$	<b>1200</b>	<b>V</b>
$I_F, T_c \leq 135^\circ\text{C}$	<b>40</b>	<b>A</b>
$Q_c$	<b>232</b>	<b>nC</b>

**Benefits**

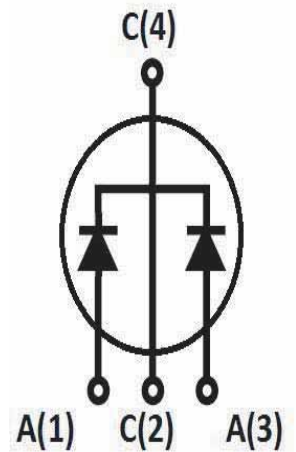
- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

**Applications**

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV



Package:  
TO-247



Part No.	Package Type	Marking
SC3S12040B	TO-247-3 pin	SC12040

## Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$		1200	V
Surge Peak Reverse Voltage	$V_{RSM}$		1200	
DC Blocking Voltage	$V_{DC}$		1200	
Continuous Forward Current	$I_F$	$T_C=25^{\circ}C$ $T_C=135^{\circ}C$	44* 20*	A
Repetitive Peak Forward Surge Current	$I_{FRM}$	$T_C=25^{\circ}C$ , $t_p=10ms$ , Half Sine Wave, $D=0.3$	100*	A
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	$T_C=25^{\circ}C$ , $t_p=10ms$ , Half Sine Wave	140*	A
Power Dissipation	$P_{TOT}$	$T_C=25^{\circ}C$	192.3*	W
		$T_C=110^{\circ}C$	85	W
Operating Junction	$T_j$		-55 $^{\circ}C$ to 175 $^{\circ}C$	$^{\circ}C$
Storage Temperature	$T_{stg}$		-55 $^{\circ}C$ to 175 $^{\circ}C$	$^{\circ}C$
Mounting Torque		M3 Screw 6-32 Screw	1	Nm lbf-in
			8.8	

\* Per leg ; \*\* Per diode

## Thermal Characteristics

Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	$R_{thJC}$		0.78* 0.39**	$^{\circ}C/W$

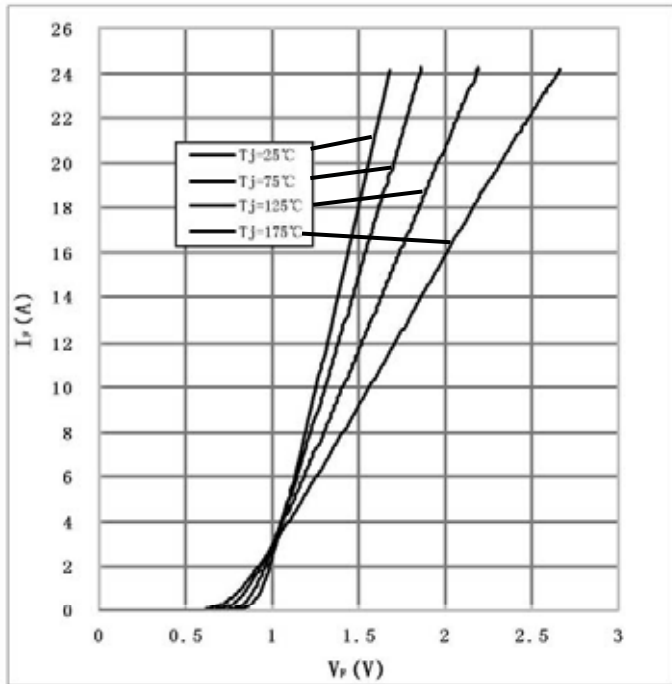
\* Per leg ; \*\* Per diode

## Electrical Characteristics

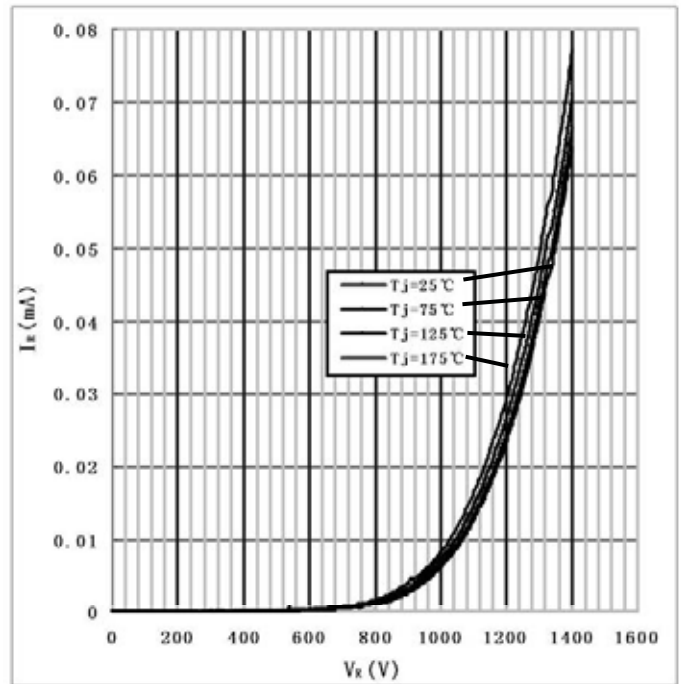
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	$V_F$	$I_F=20A$ , $T_j=25^{\circ}C$	1.6	1.8	V
		$I_F=20A$ , $T_j=175^{\circ}C$	2.4	3	
Reverse Current	$I_R$	$V_R=1200V$ , $T_j=25^{\circ}C$	50	100	$\mu A$
		$V_R=1200V$ , $T_j=175^{\circ}C$	100	200	
Total Capacitive Charge	$Q_C$	$V_R=800V$ , $T_j=150^{\circ}C$ $Q_C = \int_0^{V_R} C(V)dV$	116	-	nC
Total Capacitance	C	$V_R=0V$ , $T_j=25^{\circ}C$ , $f=1MHz$	1640	1800	pF
		$V_R=400V$ , $T_j=25^{\circ}C$ , $f=1MHz$	105	108	
		$V_R=800V$ , $T_j=25^{\circ}C$ , $f=1MHz$	103	104	

## RATING AND CHARACTERISTICS CURVES(SC3S12040B)

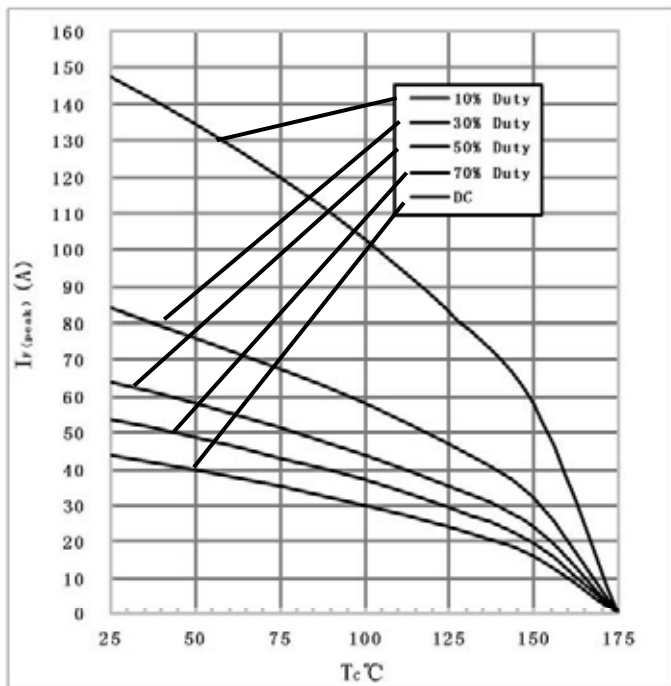
1) Forward IV characteristics as a function of  $T_j$  :



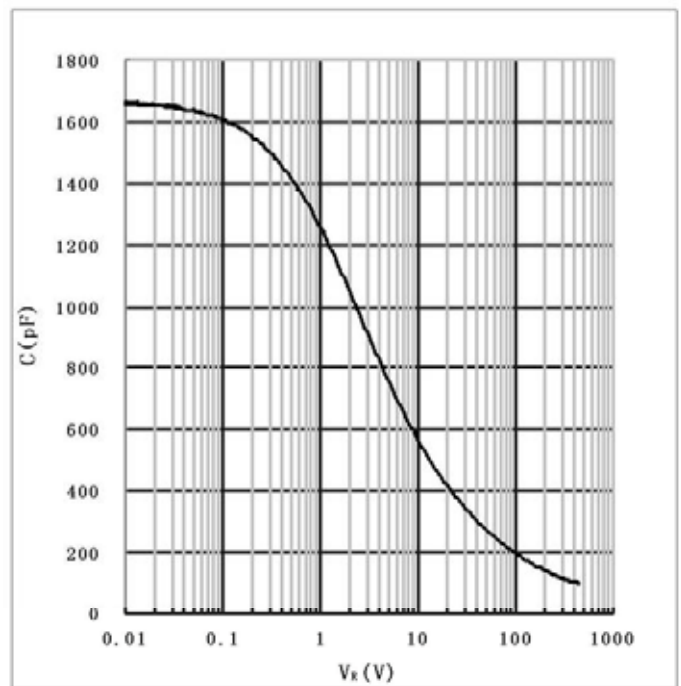
2) Reverse IV characteristics as a function of  $T_j$  :



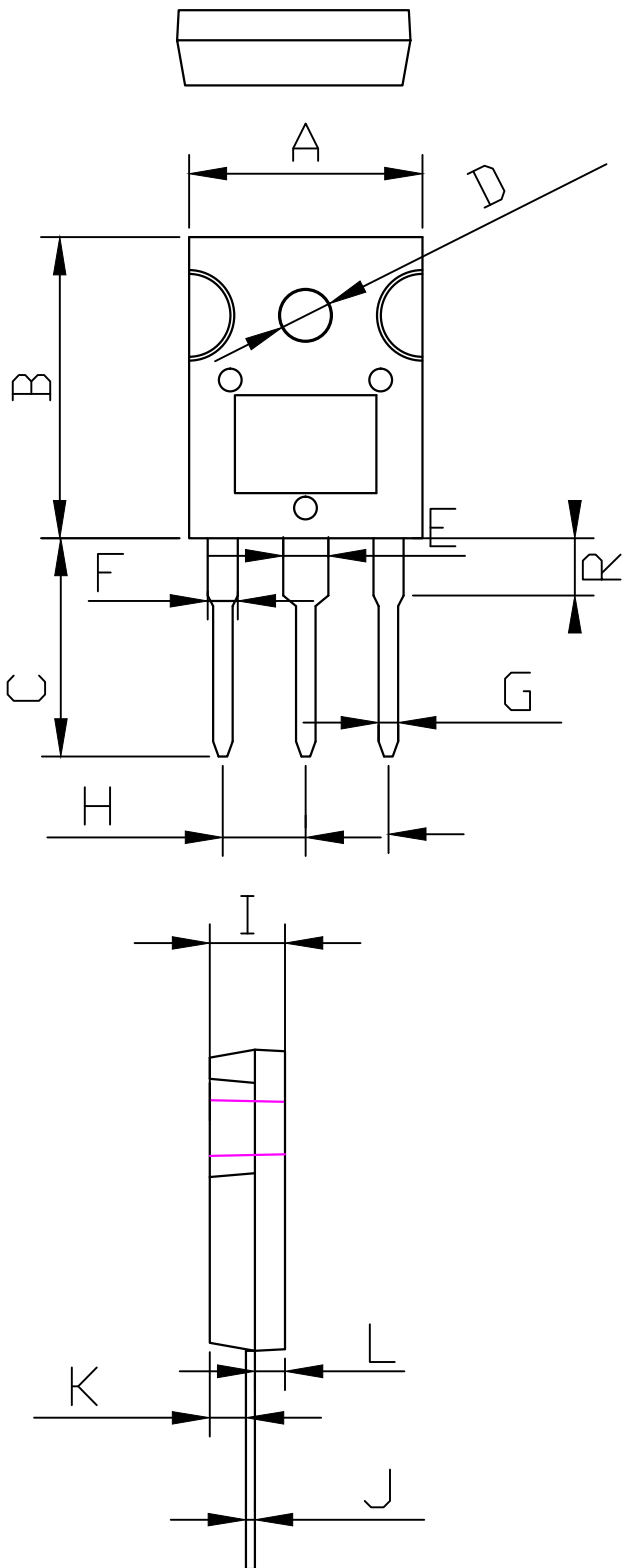
3) Current Derating



4) Capacitance vs. reverse voltage :



TO-247



项目	mm		
	标准值	Min	Max
A	15.5	15.45	15.55
B	20	19.9	20.1
C	14.5	14.4	14.6
D	3.5	3.3	3.6
E	3	2.95	3.05
F	2	1.95	2.05
G	1.3	1.2	1.4
H	5.5	5.4	5.6
I	5	4.95	5.05
J	0.6	0.58	0.62
K	2.4	2.3	2.5
L	2	1.9	2.1
R	3.8	3.6	4